

Schottky Barrier (Double) Diodes

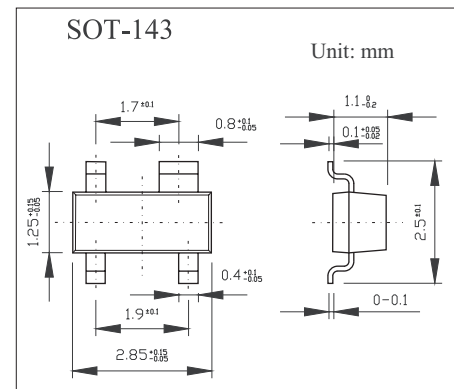
BAS40-07

■ Features

- Low forward voltage
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	MIN	MAX	Unit
continuous reverse voltage	V_R			40	V
continuous forward current	I_F			120	mA
repetitive peak forward current	I_{FRM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		120	mA
non-repetitive peak forward current	I_{FSM}	$t_p < 10 \text{ ms}$		200	A
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			150	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$
thermal resistance from junction to ambient	$R_{th\ j-a}$			500	K/W



BAS40-07■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Max	Unit
forward voltage	V_F	$I_F = 1\text{ mA}$		380	mV
		$I_F = 10\text{ mA}$		500	mV
		$I_F = 40\text{ mA}$		1	V
reverse current	I_R	$V_R = 30\text{ V}; \text{note 1}$		1	nA
		$V_R = 40\text{ V}; \text{note 1}$		10	$\mu\text{ A}$
diode capacitance	C_d	$f = 1\text{ MHz}; V_R = 0$		5	pF

Note

1. Pulse test: $t_p = 300\text{ ms}$; $\delta = 0.02$.

■ Marking

Marking	47
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